3.3 V LVTTL/LVCMOS to **Differential LVECL Translator**

Description

The MC100EPT24 is a LVTTL/LVCMOS to differential LVECL translator. Because LVECL levels and LVTTL/LVCMOS levels are used, a -3.3 V, +3.3 V and ground are required. The small outline 8-lead package and the single gate of the EPT24 makes it ideal for those applications where space, performance, and low power are at a premium.

Features

- 350 ps Typical Propagation Delay
- Maximum Input Clock Frequency = > 1.0 GHz Typical
- The 100 Series Contains Temperature Compensation
- Operating Range:

 $V_{CC} = 3.0 \text{ V}$ to 3.6 V; $V_{EE} = -3.6 \text{ V}$ to -3.0 V; GND = 0 V

- PNP LVTTL Input for Minimal Loading
- Q Output will Default HIGH with Input Open
- These Devices are Pb-Free, Halogen Free and are RoHS Compliant



ON Semiconductor®

www.onsemi.com







SOIC-8 NB **D SUFFIX**

TSSOP-8 **DT SUFFIX**

MN SUFFIX CASE 751-07 CASE 948R-02 CASE 506AA

MARKING DIAGRAMS*







SOIC-8 NB

TSSOP-8

DFN8

= Assembly Location Α

= Wafer Lot L = Year Υ W = Work Week = Date Code = Pb-Free Package

(Note: Microdot may be in either location)

ORDERING INFORMATION

Device	Package	Shipping†
MC100EPT24DG	SOIC-8 NB (Pb-Free)	98 Units / Tube
MC100EPT24DR2G	SOIC-8 NB (Pb-Free)	2500 Tape & Reel
MC100EPT24DTG	TSSOP-8 (Pb-Free)	100 Units / Tube
MC100EPT24MNR4G	DFN8 (Pb-Free)	1000 Tape & Reel

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

^{*}For additional marking information, refer to Application Note AND8002/D.

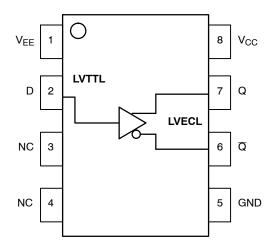


Figure 1. 8-Lead Pinout (Top View) and Logic Diagram

Table 1. PIN DESCRIPTION

PIN	FUNCTION
Q, Q	Differential LVECL Outputs
D	LVTTL Input
V _{CC}	Positive Supply
GND	Ground
V _{EE}	Negative Supply
NC	No Connect
EP	(DFN8 only) Thermal exposed pad must be connected to a sufficient ther- mal conduit. Electrically connect to the most negative supply (GND) or leave unconnected, floating open.

Table 2. ATTRIBUTES

Characteristics	Value				
Internal Input Pulldown Resistor	N/A				
Internal Input Pullup Resistor	N/A				
ESD Protection Human Body Model Machine Model Charged Device Model	> 4 kV > 200 V > 2 kV				
Moisture Sensitivity, Indefinite Time Out of Drypack (Note 1)	Pb-Free Pkg				
SOIC-8 NB TSSOP-8 DFN8	Level 1 Level 3 Level 1				
Flammability Rating Oxygen Index: 28 to 34	UL 94 V-0 @ 0.125 in				
Transistor Count	181 Devices				
Meets or exceeds JEDEC Spec EIA/JESD78 IC Latchup Test					

^{1.} For additional information, see Application Note AND8003/D.

Table 3. MAXIMUM RATINGS

Symbol	Parameter	Condition 1	Condition 2	Rating	Unit
V_{CC}	Positive Power Supply	GND = 0 V	V _{EE} = -3.3V	3.8	V
V _{EE}	Negative Power Supply	GND = 0 V	V _{CC} = 3.3V	-3.8	V
V _{IN}	Input Voltage	GND = 0 V	$V_{I} \le V_{CC}$	0 to V _{CC}	V
l _{out}	Output Current	Continuous Surge		50 100	mA
T _A	Operating Temperature Range			-40 to +85	°C
T _{stg}	Storage Temperature Range			-65 to +150	°C
$\theta_{\sf JA}$	Thermal Resistance (Junction-to-Ambient)	0 lfpm 50 lfpm	SOIC-8 NB SOIC-8 NB	190 130	°C/W
$\theta_{\sf JC}$	Thermal Resistance (Junction-to-Case)	Standard Board	SOIC-8 NB	41 to 44	°C/W
θ_{JA}	Thermal Resistance (Junction-to-Ambient)	0 lfpm 50 lfpm	TSSOP-8 TSSOP-8	185 140	°C/W
$\theta_{\sf JC}$	Thermal Resistance (Junction-to-Case)	Standard Board	TSSOP-8	41 to 44	°C/W
$\theta_{\sf JA}$	Thermal Resistance (Junction-to-Ambient)	0 lfpm 50 lfpm	DFN8 DFN8	129 84	°C/W
T _{sol}	Wave Solder (Pb-Free)			265	°C
$\theta_{\sf JC}$	Thermal Resistance (Junction-to-Case)	(Note 1)	DFN8	35 to 40	°C/W

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

Table 4. LVTTL INPUT DC CHARACTERISTICS ($V_{CC} = 3.3 \text{ V}$, $V_{EE} = -3.6 \text{ V}$ to -3.0 V, GND = 0.0 V; $T_A = -40 ^{\circ}\text{C}$ to $85 ^{\circ}\text{C}$)

Symbol	Characteristic	Condition	Min	Тур	Max	Unit
I _{IH}	Input HIGH Current	V _{IN} = 2.7 V			20	μΑ
I _{IHH}	Input HIGH Current HIGH Voltage	V _{CC} = V _{IN} = 3.8 V			100	μΑ
I _{IL}	Input LOW Current	V _{IN} = 0.5 V			-0.6	mA
V _{IK}	Input Clamp Voltage	I _{IN} = -18 mA			-1.0	V
V _{IH}	Input HIGH Voltage		2.0			V
V_{IL}	Input LOW Voltage				0.8	V

NOTE: Device will meet the specifications after thermal equilibrium has been established when mounted in a test socket or printed circuit board with maintained transverse airflow greater than 50 lfpm. Electrical parameters are guaranteed only over the declared operating temperature range. Functional operation of the device exceeding these conditions is not implied. Device specification limit values are applied individually under normal operating conditions and not valid simultaneously.

Table 5. NECL OUTPUT DC CHARACTERISTICS ($V_{CC} = 3.3 \text{ V}, V_{EE} = -3.3 \text{ V}, \text{GND} = 0.0 \text{ V} \text{ (Note 1))}$

		-40°C		25°C		85°C					
Symbol	Characteristic	Min	Тур	Max	Min	Тур	Max	Min	Тур	Max	Unit
V _{OH}	Output HIGH Voltage (Note 2)	-1145	-1020	-895	-1145	-1020	-895	-1145	-1030	-895	mV
V _{OL}	Output LOW Voltage (Note 2)	-1945	-1820	-1695	-1945	-1820	-1695	-1945	-1820	-1695	mV
I _{CC}	Positive Power Supply Current		2.0	4.0		2.0	4.0		2.0	4.0	mA
I _{EE}	Negative Power Supply Current	20	30	38	20	30	38	20	30	38	mA

NOTE: Device will meet the specifications after thermal equilibrium has been established when mounted in a test socket or printed circuit board with maintained transverse airflow greater than 50 lfpm. Electrical parameters are guaranteed only over the declared operating temperature range. Functional operation of the device exceeding these conditions is not implied. Device specification limit values are applied individually under normal operating conditions and not valid simultaneously.

- 1. Output levels will vary 1:1 with GND. $V_{\mbox{\footnotesize EE}}$ can vary $\pm\,0.3$ V.
- 2. Outputs are terminated through a 50 Ω resistor to GND 2 V.

^{1.} JEDEC standard multilayer board - 2S2P (2 signal, 2 power)

Table 6. AC CHARACTERISTICS ($V_{CC} = 0 \text{ V}$; $V_{EE} = -3.0 \text{ V}$ to -5.5 V or $V_{CC} = 3.0 \text{ V}$ to 5.5 V; $V_{EE} = 0 \text{ V}$ (Note 1))

		-40°C		25°C		85°C					
Symbol	Characteristic	Min	Тур	Max	Min	Тур	Max	Min	Тур	Max	Unit
f _{max}	Maximum Input Clock Frequency (Figure 2)		> 1			> 1			> 1		GHz
t _{PLH} , t _{PHL}	0 1 1 1 10 11 1 10 10 10 10 10 10 10 10		500	800	300	530	800	300	560	800	ps
t _{JITTER}	RMS Random Clock Jitter (Figure 2)		0.2	< 1		0.2	< 1		0.2	< 1	ps
t _r t _f	Output Rise/Fall Times Q, Q (20% – 80%) @ 50 MHz	70	125	170	80	130	180	100	150	200	ps

NOTE: Device will meet the specifications after thermal equilibrium has been established when mounted in a test socket or printed circuit board with maintained transverse airflow greater than 50 lfpm. Electrical parameters are guaranteed only over the declared operating temperature range. Functional operation of the device exceeding these conditions is not implied. Device specification limit values are applied individually under normal operating conditions and not valid simultaneously.

- 1. Measured using a LVTTL source, 50% duty cycle clock source. All loading with 50 Ω to GND 2.0 V.
- 2. Specifications for standard TTL input signal.

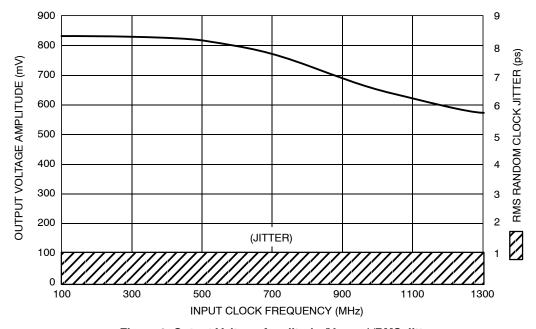


Figure 2. Output Voltage Amplitude (V_{OUTpp})/RMS Jitter vs. Input Clock Frequency at Ambient Temperature

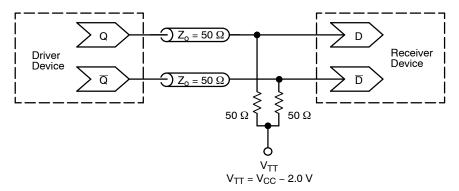


Figure 3. Typical Termination for Output Driver and Device Evaluation (See Application Note <u>AND8020/D</u> – Termination of ECL Logic Devices)

Resource Reference of Application Notes

AN1405/D - ECL Clock Distribution Techniques

AN1406/D - Designing with PECL (ECL at +5.0 V)

AN1503/D - ECLinPS™ I/O SPICE Modeling Kit

AN1504/D - Metastability and the ECLinPS Family

AN1568/D - Interfacing Between LVDS and ECL

AND8001/D - The ECL Translator Guide

AND8001/D - Odd Number Counters Design

AND8002/D - Marking and Date Codes

AND8020/D – Termination of ECL Logic Devices

AND8066/D - Interfacing with ECLinPS

AND8090/D - AC Characteristics of ECL Devices

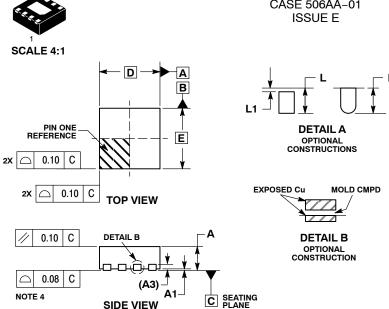
ECLinPS is a trademark of Semiconductor Components Industries, LLC (SCILLC) or its subsidiaries in the United States and/or other countries.

DETAIL A

е

- D2 →

BOTTOM VIEW



0.10 C

Ф

AB

0.05 C NOTE 3



DATE 22 JAN 2010

- DIMENSIONING AND TOLERANCING PER
- ASME Y14.5M, 1994 . CONTROLLING DIMENSION: MILLIMETERS.
- DIMENSION b APPLIES TO PLATED TERMINAL AND IS MEASURED BETWEEN
- 0.15 AND 0.20 MM FROM TERMINAL TIP. COPLANARITY APPLIES TO THE EXPOSED PAD AS WELL AS THE TERMINALS.

	MILLIMETERS						
DIM	MIN	MAX					
Α	0.80	1.00					
A1	0.00	0.05					
А3	0.20	REF					
b	0.20	0.30					
D	2.00	BSC					
D2	1.10	1.30					
E	2.00	BSC					
E2	0.70	0.90					
е	0.50 BSC						
K	0.30 REF						
L	0.25 0.35						
11		0.10					

GENERIC MARKING DIAGRAM*



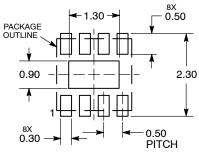
XX = Specific Device Code

= Date Code

= Pb-Free Device

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot " ■", may or may not be present.

RECOMMENDED SOLDERING FOOTPRINT*



DIMENSIONS: MILLIMETERS

*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

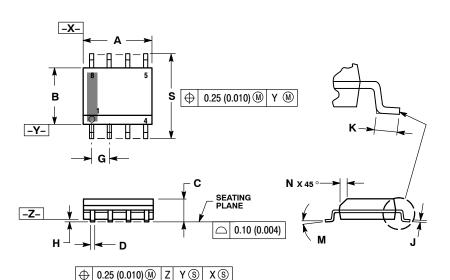
DOCUMENT NUMBER:	98AON18658D	Electronic versions are uncontrolled except when accessed directly from the Document Repositor Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red.			
DESCRIPTION:	DFN8, 2.0X2.0, 0.5MM PITO	CH	PAGE 1 OF 1		

ON Semiconductor and unare trademarks of Semiconductor Components Industries, LLC dba ON Semiconductor or its subsidiaries in the United States and/or other countries. ON Semiconductor reserves the right to make changes without further notice to any products herein. ON Semiconductor makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does ON Semiconductor assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. ON Semiconductor does not convey any license under its patent rights nor the rights of others.



SOIC-8 NB CASE 751-07 **ISSUE AK**

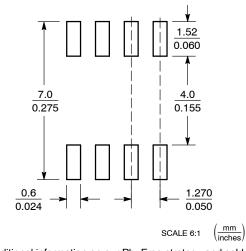
DATE 16 FEB 2011



- NOTES:
 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
 CONTROLLING DIMENSION: MILLIMETER.
- DIMENSION A AND B DO NOT INCLUDE MOLD PROTRUSION.
- MAXIMUM MOLD PROTRUSION 0.15 (0.006) PER SIDE
- DIMENSION D DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.127 (0.005) TOTAL IN EXCESS OF THE D DIMENSION AT MAXIMUM MATERIAL CONDITION.
- 751-01 THRU 751-06 ARE OBSOLETE. NEW STANDARD IS 751-07.

	MILLIMETERS		INCHES		
DIM	MIN	MAX	MIN	MAX	
Α	4.80	5.00	0.189	0.197	
В	3.80	4.00	0.150	0.157	
С	1.35	1.75	0.053	0.069	
D	0.33	0.51	0.013	0.020	
G	1.27	7 BSC	0.050 BSC		
Н	0.10	0.25	0.004	0.010	
J	0.19	0.25	0.007	0.010	
K	0.40	1.27	0.016	0.050	
М	0 °	8 °	0 °	8 °	
N	0.25	0.50	0.010	0.020	
S	5.80	6.20	0.228	0.244	

SOLDERING FOOTPRINT*



^{*}For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

GENERIC MARKING DIAGRAM*



XXXXX = Specific Device Code = Assembly Location = Wafer Lot = Year

= Work Week = Pb-Free Package XXXXXX AYWW AYWW \mathbb{H} H Discrete **Discrete** (Pb-Free)

XXXXXX = Specific Device Code = Assembly Location Α

ww = Work Week = Pb-Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "•", may or may not be present. Some products may not follow the Generic Marking.

STYLES ON PAGE 2

DOCUMENT NUMBER:	98ASB42564B	Electronic versions are uncontrolled except when accessed directly from the Document Repos Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red.			
DESCRIPTION:	SOIC-8 NB		PAGE 1 OF 2		

ON Semiconductor and (III) are trademarks of Semiconductor Components Industries, LLC dba ON Semiconductor or its subsidiaries in the United States and/or other countries. ON Semiconductor reserves the right to make changes without further notice to any products herein. ON Semiconductor makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does ON Semiconductor assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. ON Semiconductor does not convey any license under its patent rights nor the

SOIC-8 NB CASE 751-07 ISSUE AK

DATE 16 FEB 2011

STYLE 1: PIN 1. EMITTER 2. COLLECTOR 3. COLLECTOR 4. EMITTER 5. EMITTER 6. BASE 7. BASE 8. EMITTER	STYLE 2: PIN 1. COLLECTOR, DIE, #1 2. COLLECTOR, #1 3. COLLECTOR, #2 4. COLLECTOR, #2 5. BASE, #2 6. EMITTER, #2 7. BASE, #1 8. EMITTER, #1	STYLE 3: PIN 1. DRAIN, DIE #1 2. DRAIN, #1 3. DRAIN, #2 4. DRAIN, #2 5. GATE, #2 6. SOURCE, #2 7. GATE, #1 8. SOURCE, #1	STYLE 4: PIN 1. ANODE 2. ANODE 3. ANODE 4. ANODE 5. ANODE 6. ANODE 7. ANODE 8. COMMON CATHODE
STYLE 5: PIN 1. DRAIN 2. DRAIN 3. DRAIN 4. DRAIN 5. GATE 6. GATE 7. SOURCE 8. SOURCE	7. BASE, #1 8. EMITTER, #1 STYLE 6: PIN 1. SOURCE 2. DRAIN 3. DRAIN 4. SOURCE 5. SOURCE 6. GATE 7. GATE 8. SOURCE	STYLE 7: PIN 1. INPUT 2. EXTERNAL BYPASS 3. THIRD STAGE SOURCE 4. GROUND 5. DRAIN 6. GATE 3 7. SECOND STAGE Vd 8. FIRST STAGE Vd	STYLE 8: PIN 1. COLLECTOR, DIE #1 2. BASE, #1 3. BASE, #2
STYLE 9: PIN 1. EMITTER, COMMON 2. COLLECTOR, DIE #1 3. COLLECTOR, DIE #2 4. EMITTER, COMMON 5. EMITTER, COMMON 6. BASE, DIE #2 7. BASE, DIE #1 8. EMITTER, COMMON	STYLE 10: PIN 1. GROUND 2. BIAS 1 3. OUTPUT 4. GROUND 5. GROUND 6. BIAS 2 7. INPUT 8. GROUND	STYLE 11: PIN 1. SOURCE 1 2. GATE 1 3. SOURCE 2 4. GATE 2 5. DRAIN 2 6. DRAIN 2 7. DRAIN 1 8. DRAIN 1	STYLE 12: PIN 1. SOURCE 2. SOURCE 3. SOURCE 4. GATE 5. DRAIN 6. DRAIN 7. DRAIN 8. DRAIN
STYLE 13: PIN 1. N.C. 2. SOURCE 3. SOURCE 4. GATE 5. DRAIN 6. DRAIN 7. DRAIN 8. DRAIN	STYLE 14: PIN 1. N-SOURCE 2. N-GATE 3. P-SOURCE 4. P-GATE 5. P-DRAIN 6. P-DRAIN 7. N-DRAIN 8. N-DRAIN	STYLE 15: PIN 1. ANODE 1 2. ANODE 1 3. ANODE 1 4. ANODE 1 5. CATHODE, COMMON 6. CATHODE, COMMON 7. CATHODE, COMMON 8. CATHODE, COMMON	STYLE 16: PIN 1. EMITTER, DIE #1 2. BASE, DIE #1 3. EMITTER, DIE #2 4. BASE, DIE #2 5. COLLECTOR, DIE #2 6. COLLECTOR, DIE #2 7. COLLECTOR, DIE #1 8. COLLECTOR, DIE #1
STYLE 17: PIN 1. VCC 2. V2OUT 3. V1OUT 4. TXE 5. RXE 6. VEE 7. GND 8. ACC	STYLE 18: PIN 1. ANODE 2. ANODE 3. SOURCE 4. GATE 5. DRAIN 6. DRAIN 7. CATHODE 8. CATHODE	STYLE 19: PIN 1. SOURCE 1 2. GATE 1 3. SOURCE 2 4. GATE 2 5. DRAIN 2 6. MIRROR 2 7. DRAIN 1 8. MIRROR 1	STYLE 20: PIN 1. SOURCE (N) 2. GATE (N) 3. SOURCE (P) 4. GATE (P) 5. DRAIN 6. DRAIN 7. DRAIN 8. DRAIN
5. RXE 6. VEE 7. GND 8. ACC STYLE 21: PIN 1. CATHODE 1 2. CATHODE 2 3. CATHODE 3 4. CATHODE 4 5. CATHODE 5 6. COMMON ANODE 7. COMMON ANODE 8. CATHODE 6	STYLE 22: PIN 1. I/O LINE 1 2. COMMON CATHODE/VCC 3. COMMON CATHODE/VCC 4. I/O LINE 3 5. COMMON ANODE/GND 6. I/O LINE 4 7. I/O LINE 5 8. COMMON ANODE/GND	STYLE 23: PIN 1. LINE 1 IN 2. COMMON ANODE/GND 3. COMMON ANODE/GND 4. LINE 2 IN 5. LINE 2 OUT 6. COMMON ANODE/GND 7. COMMON ANODE/GND 8. LINE 1 OUT	STYLE 24: PIN 1. BASE 2. EMITTER 3. COLLECTOR/ANODE 4. COLLECTOR/ANODE 5. CATHODE 6. CATHODE 7. COLLECTOR/ANODE 8. COLLECTOR/ANODE
STYLE 25: PIN 1. VIN 2. N/C 3. REXT 4. GND 5. IOUT 6. IOUT 7. IOUT 8. IOUT	STYLE 26: PIN 1. GND 2. dv/dt 3. ENABLE 4. ILIMIT 5. SOURCE 6. SOURCE 7. SOURCE 8. VCC	STYLE 27: PIN 1. ILIMIT 2. OVLO 3. UVLO 4. INPUT+ 5. SOURCE 6. SOURCE 7. SOURCE 8. DRAIN	STYLE 28: PIN 1. SW_TO_GND 2. DASIC_OFF 3. DASIC_SW_DET 4. GND 5. V_MON 6. VBULK 7. VBULK 8. VIN
STYLE 29: PIN 1. BASE, DIE #1 2. EMITTER, #1 3. BASE, #2 4. EMITTER, #2 5. COLLECTOR, #2 6. COLLECTOR, #2 7. COLLECTOR, #1 8. COLLECTOR, #1	STYLE 30: PIN 1. DRAIN 1 2. DRAIN 1 3. GATE 2 4. SOURCE 2 5. SOURCE 1/DRAIN 2 6. SOURCE 1/DRAIN 2 7. SOURCE 1/DRAIN 2 8. GATE 1		

DOCUMENT NUMBER:	98ASB42564B	Printed versions are uncontrolled except when accessed directly from the Document Repository. Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red.		
DESCRIPTION:	SOIC-8 NB		PAGE 2 OF 2	

ON Semiconductor and IN are trademarks of Semiconductor Components Industries, LLC dba ON Semiconductor or its subsidiaries in the United States and/or other countries. ON Semiconductor reserves the right to make changes without further notice to any products herein. ON Semiconductor makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does ON Semiconductor assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. ON Semiconductor does not convey any license under its patent rights nor the rights of others.

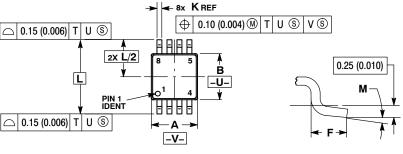


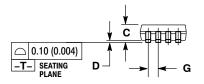


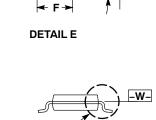
TSSOP 8 CASE 948R-02 ISSUE A

DATE 04/07/2000

SCALE 2:1







DETAIL E

- NOTES:

 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.

 2. CONTROLLING DIMENSION: MILLIMETER.

 3. DIMENSION A DOES NOT INCLUDE MOLD FLASH. PROTRUSIONS OR GATE BURRS. MOLD FLASH. OR GATE BURRS SHALL NOT EXCEED 0.15
- (0.006) PER SIDE.
 4. DIMENSION B DOES NOT INCLUDE INTERLEAD FLASH OR PROTRUSION. INTERLEAD FLASH OR PROTRUSION SHALL NOT EXCEED 0.25 (0.010) PER SIDE.
 5. TERMINAL NUMBERS ARE SHOWN FOR
- REFERENCE ONLY.
 6. DIMENSION A AND B ARE TO BE DETERMINED AT DATUM PLANE -W-.

	MILLIMETERS		INCHES	
DIM	MIN	MAX	MIN	MAX
Α	2.90	3.10	0.114	0.122
В	2.90	3.10	0.114	0.122
С	0.80	1.10	0.031	0.043
D	0.05	0.15	0.002	0.006
F	0.40	0.70	0.016	0.028
G	0.65 BSC		0.026 BSC	
K	0.25	0.40	0.010	0.016
L	4.90 BSC		0.193 BSC	
М	0°	6 °	0°	6°

DOCUMENT NUMBER:	98AON00236D	Electronic versions are uncontrolled except when accessed directly from the Document Repository. Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red.		
DESCRIPTION:	TSSOP 8		PAGE 1 OF 1	

ON Semiconductor and (III) are trademarks of Semiconductor Components Industries, LLC dba ON Semiconductor or its subsidiaries in the United States and/or other countries. ON Semiconductor reserves the right to make changes without further notice to any products herein. ON Semiconductor makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does ON Semiconductor assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. ON Semiconductor does not convey any license under its patent rights nor the rights of others.

onsemi, ONSEMI, and other names, marks, and brands are registered and/or common law trademarks of Semiconductor Components Industries, LLC dba "onsemi" or its affiliates and/or subsidiaries in the United States and/or other countries. onsemi owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of onsemi's product/patent coverage may be accessed at www.onsemi.com/site/pdf/Patent-Marking.pdf. onsemi reserves the right to make changes at any time to any products or information herein, without notice. The information herein is provided "as-is" and onsemi makes no warranty, representation or guarantee regarding the accuracy of the information, product features, availability, functionality, or suitability of its products for any particular purpose, nor does onsemi assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. Buyer is responsible for its products and applications using **onsemi** products, including compliance with all laws, regulations and safety requirements or standards, regardless of any support or applications information provided by **onsemi**. "Typical" parameters which may be provided in **onsemi** data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. **onsemi** does not convey any license under any of its intellectual property rights nor the rights of others. **onsemi** products are not designed, intended, or authorized for use as a critical component in life support systems or any FDA Class 3 medical devices or medical devices with a same or similar classification in a foreign jurisdiction or any devices intended for implantation in the human body. Should Buyer purchase or use **onsemi** products for any such unintended or unauthorized application, Buyer shall indemnify and hold **onsemi** and its officers, employees, subsidiaries, affiliates, and distributors harmless against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized use, even if such claim alleges that **onsemi** was negligent regarding the design or manufacture of the part. **onsemi** is an Equal Opportunity/Affirmative Action Employer. This literature is subject to all applicable copyright laws and is not for resale in any manner.

PUBLICATION ORDERING INFORMATION

LITERATURE FULFILLMENT: Email Requests to: orderlit@onsemi.com

onsemi Website: www.onsemi.com

TECHNICAL SUPPORT North American Technical Support: Voice Mail: 1 800–282–9855 Toll Free USA/Canada Phone: 011 421 33 790 2910

Europe, Middle East and Africa Technical Support:

Phone: 00421 33 790 2910

For additional information, please contact your local Sales Representative